

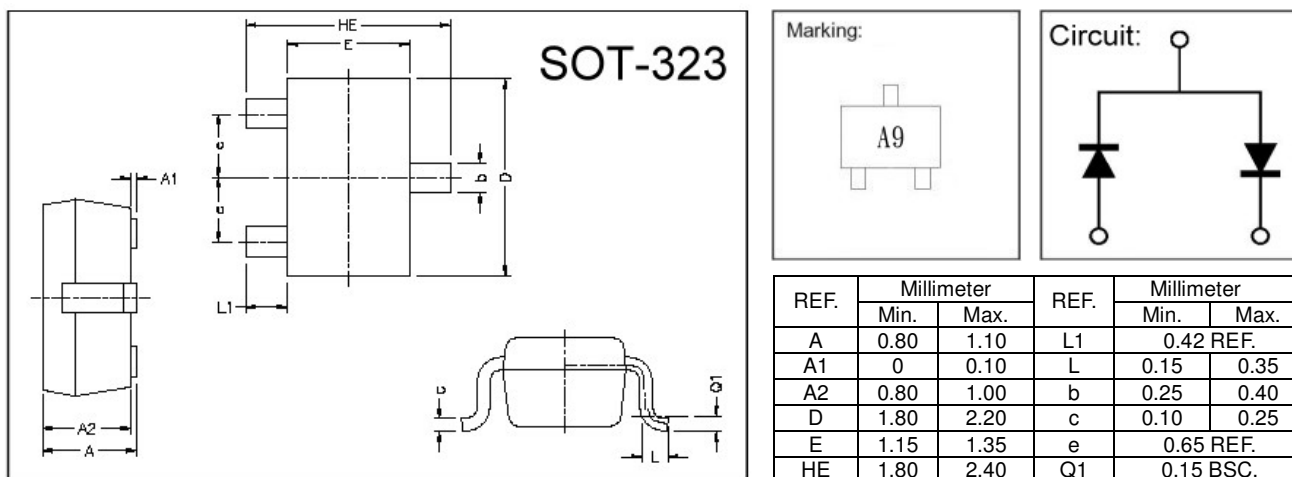
GSN217U

SURFACE MOUNT, SWITCHING DIODE
VOLTAGE 80V, CURRENT 0.1A

Description

The GSN217U is designed for ultra high speed switching.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Maximum Peak Repetitive Reverse Voltage	V _{RRM}	80	V
Maximum RMS Voltage	V _{RMS}	56	V
Maximum DC Blocking Voltage	V _{DC}	80	V
Peak Forward Surge Current at 1uSec	I _{FSM}	4.0	A
Typical Junction Capacitance between Terminal (Note 1)	C _J	2.0	pF
Maximum Average Forward Rectified Current	I _o	0.1	A
Total Power Dissipation	PD	225	mW

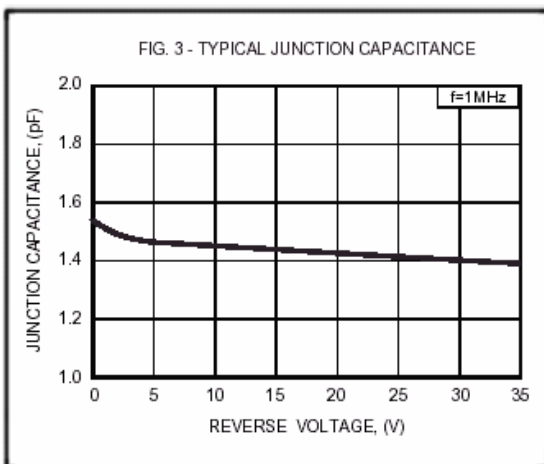
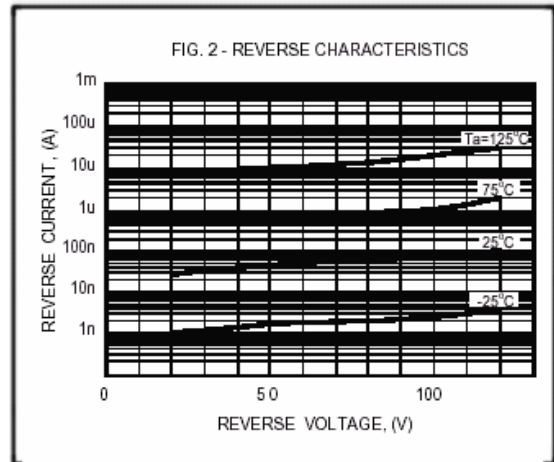
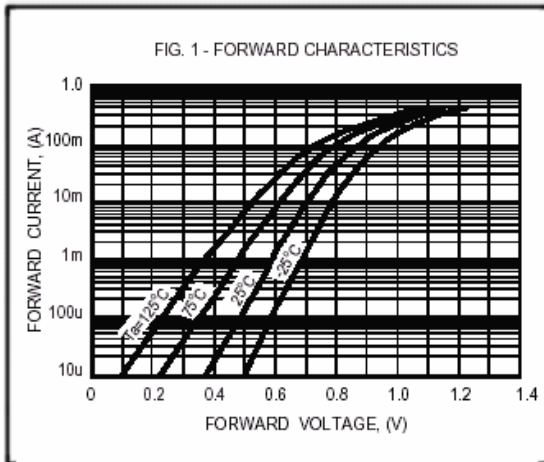
Characteristics at Ta = 25°C

Characteristics	Symbol	Typ.	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V _F	1.20	V	IF = 100mA
Maximum Average Reverse Current	IR	0.2	uA	VR = 70V

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 6.0 volt.

2. ESD sensitive product handling required.

Characteristics Curve



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